



RLT7605MG

TECHNICAL DATA

Infrared Laserdiode

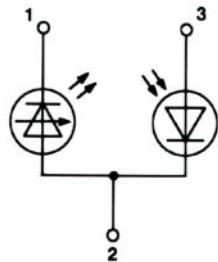
Structure: **index guided single transverse mode**

Lasing wavelength: **760 nm typ.**

Output power: **5 mW cw**

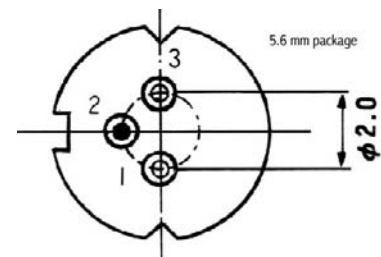
Package: **5.6 mm, TO-18**

NOTE!
LASERDIODE
MUST BE COOLED!



PIN CONNECTION:

- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Maximum Ratings (T_c = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	5	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operation Case Temperature	T _C	-10 .. +50	°C
Storage Temperature	T _{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Threshold Current	I _{th}	cw		15	20	mA
Operation Current	I _{op}	P _o = 5 mW		25	40	mA
Operating Voltage	V _{op}	P _o = 5 mW	1.8	1.9	2.0	V
Lasing Wavelength	λ _p	P _o = 5 mW	750	760	766	nm
Spectral Width	Δλ	P _o = 5 mW	0.2	0.4	1.1	nm
Beam Divergence	θ	P _o = 5 mW	7	10	12	°
Beam Divergence	θ _⊥	P _o = 5 mW	30	33	38	°
Slope Efficiency	η	cw	0.5	0.65	1	mW/mA
Monitor Current	I _m	P _o = 5 mW	250	400	800	μA